

## DS15BR400/DS15BR401

## 4-Channel LVDS Buffer/Repeater with Pre-Emphasis

### **General Description**

The DS15BR400/DS15BR401 are four channel LVDS buffer/ repeaters capable of datarates of up to 2 Gbps. High speed data paths and flow-through pinout minimize internal device jitter and simplify board layout, while pre-emphasis overcomes ISI jitter effects from lossy backplanes and cables. The differential inputs interface to LVDS, and Bus LVDS signals such as those on National's 10-, 16-, and 18- bit Bus LVDS SerDes, as well as CML and LVPECL. The differential inputs and outputs of the DS15BR400 are internally terminated with  $100\Omega$  resistors to improve performance and minimize board space. The DS15BR401 does not have input termination resistors. The repeater function is especially useful for boosting signals for longer distance transmission over lossy cables and backplanes.

The DS15BR400/DS15BR401 are powered from a single 3.3V supply and consume 578 mW (typ). They operate over the full -40°C to +85°C industrial temperature range and are available in space saving LLP-32 and TQFP-48 packages.

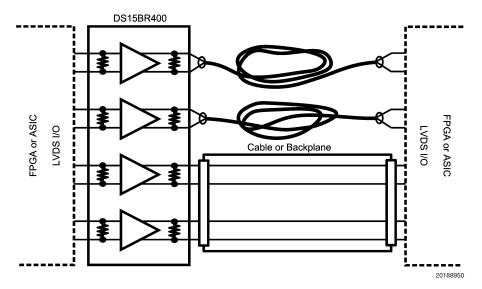
#### **Features**

- DC to 2 Gbps low jitter, high noise immunity, low power operation
- 6 dB of pre-emphasis drives lossy backplanes and cables
- LVDS/CML/LVPECL compatible input, LVDS output
- On-chip 100  $\Omega$  output termination, optional 100  $\Omega$  input termination
- 15 kV ESD protection on LVDS inputs and outputs
- Single 3.3V supply
- Industrial -40 to +85°C temperature range
- Space saving LLP-32 or TQFP-48 packages
- Evaluation Kit Available

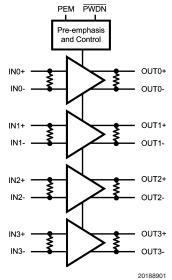
## **Applications**

- Cable extention applications
- Signal repeating and buffering
- Digital routers

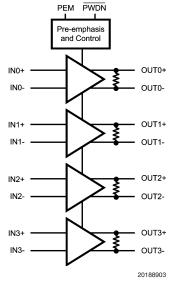
## **Typical Application**



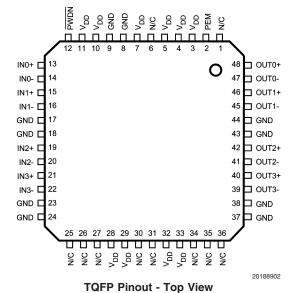
## **Block and Connection Diagrams**



DS15BR400 Block Diagram



DS15BR401 Block Diagram



GND IN0+ 9 32 OUT0+ 10 31 OUT0-IN0 30 OUT1+ IN1+ 11) 12 DAP 29 OUT1-IN1 (GND) 13 28 OUT2+ IN2+ 14) 27 OUT2-IN2-15 26 OUT3+ IN3+ IN3- 16 25 OUT3-17 18 19 20 21 22 23 24 V<sub>DD</sub> Vpp 20188912

**LLP Pinout - Top View** 

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IN0+	13	9	I, LVDS	Channel 0 inverting and non-inverting differential inputs.	
INO-	14	10			
IN1+	15	11	I, LVDS	Channel 1 inverting and non-inverting differential inputs.	
IN1-	16	12			
IN2+	19	13	I, LVDS	Channel 2 inverting and non-inverting differential inputs.	
IN2-	20	14			
IN3+	21	15	I, LVDS	Channel 3 inverting and non-inverting differential inputs.	
IN3-	22	16			
DIFFERI	ENTIAL OUTPUT	S			
OUT0+	48	32	O, LVDS	Channel 0 inverting and non-inverting differential outputs. (Note 2)	
OUT0-	47	31			
OUT1+	46	30	O, LVDS	Channel 1 inverting and non-inverting differential outputs. (Note 2)	
OUT1-	45	29			
OUT2+	42	28	O, LVDS	Channel 2 inverting and non-inverting differential outputs. (Note 2)	
OUT2-	41	27			
OUT3+	40	26	O, LVDS	Channel 3 inverting and non-inverting differential outputs. (Note 2)	
OUT3-	39	25			
DIGITAL	CONTROL INTE	RFACE			
PWDN	12	8	I, LVTTL	A logic low at PWDN activates the hardware power down mode (all	
				channels).	
PEM	2	2	I, LVTTL	Pre-emphasis Control Input (affects all Channels)	
POWER					
V <sub>DD</sub>	3, 4, 5, 7, 10,	3, 4, 6, 7,	I, Power	$V_{DD} = 3.3V, \pm 10\%$	
	11, 28, 29, 32,	20, 21			
	33				
GND	8, 9, 17, 18, 23,	5 (Note 1)	I, Ground	Ground reference for LVDS and CMOS circuitry. For the LLP package, the	
	24, 37, 38, 43,			DAP is used as the primary GND connection to the device in addition to the	
	44			pin numbers listed. The DAP is the exposed metal contact at the bottom of	
				the LLP-32 package. It should be connected to the ground plane with at	
				least 4 vias for optimal AC and thermal performance.	
N/C	1,6, 25, 26, 27,	1, 17,		No Connect	
	30, 31, 34, 35,	18,19,22,			

Note 1: Note that for the LLP package the GND is connected thru the DAP on the back side of the LLP package in addition to the actual pin numbers listed.

Note 2: The LVDS outputs do not support a multidrop (BLVDS) environment. The LVDS output characteristics of the DS15BR400 and DS15BR401 are optimized for point-to-point backplane and cable applications.

23, 24

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## **Absolute Maximum Ratings** (Note 3)

Supply Voltage ( $V_{DD}$ ) -0.3V to +4.0V CMOS Input Voltage -0.3V to ( $V_{DD}$ +0.3V) LVDS Receiver Input Voltage -0.3V to ( $V_{DD}$ +0.3V) LVDS Driver Output Voltage -0.3V to ( $V_{DD}$ +0.3V) LVDS Output Short Circuit Current +40 mA Junction Temperature +150°C

Lead Temperature (Solder, 4sec) 260°C

Max Pkg Power Capacity @ 25°C

TQFP 1.64W LLP 4.16W

Thermal Resistance ( $\theta_{JA}$ )

Storage Temperature

TQFP 76°C/W LLP 30°C/W

Package Derating above +25°C

TQFP 13.2mW/°C LLP 33.3mW/°C

ESD Last Passing Voltage

HBM, 1.5kΩ, 100pF 8 kV

LVDS pins to GND only 15 kV EIAJ,  $0\Omega$ , 200pF 250V Charged Device Model 1000V

# Recommended Operating Conditions

Operating Temperature (T<sub>A</sub>)

Industrial -40°C to +85°C

Note 3: Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation of products outside of recommended operation conditions.

Note 4: V<sub>ID</sub> max < 2.4V

### **Electrical Characteristics**

Over recommended operating supply and temperature ranges unless other specified.

-65°C to +150°C

Symbol	Parameter	Conditions	Min	Typ (Note 5)	Max	Units
LVCMOS	LVCMOS DC SPECIFICATIONS (PWDN, PEM)					
V <sub>IH</sub>	High Level Input Voltage		2.0		$V_{DD}$	V
V <sub>IL</sub>	Low Level Input Voltage		GND		0.8	V
I <sub>IH</sub>	High Level Input Current	$V_{IN} = V_{DD} = 3.6V (\overline{PWDN} \text{ pin})$	-10		+10	μA
I <sub>IHR</sub>	High Level Input Current	$V_{IN} = V_{DD} = 3.6V (PEM pin)$	40		200	μA
I <sub>IL</sub>	Low Level Input Current	$V_{IN} = V_{SS}, V_{DD} = 3.6V$	-10		+10	μA
C <sub>IN1</sub>	LVCMOS Input Capacitance	Any Digital Input Pin to V <sub>SS</sub>		5.5		pF
V <sub>CL</sub>	Input Clamp Voltage	$I_{CL} = -18 \text{ mA}, V_{DD} = 0V$	-1.5	-0.8		V
LVDS INPUT DC SPECIFICATIONS (INn±)						
V <sub>TH</sub>	Differential Input High	$V_{CM} = 0.8V \text{ to } 3.55V,$		0	100	mV
	Threshold (Note 6)	$V_{DD} = 3.6V$		U	100	IIIV
$V_{TL}$	Differential Input Low	$V_{CM} = 0.8V \text{ to } 3.55V,$ $-100$		0		mV
	Threshold (Note 6)	$V_{DD} = 3.6V$	-100	O		1110
$V_{ID}$	Differential Input Voltage	$V_{CM} = 0.8V \text{ to } 3.55V, V_{DD} = 3.6V$	100		2400	mV
$V_{CMR}$	Common Mode Voltage	$V_{ID} = 150 \text{ mV}, V_{DD} = 3.6 \text{V}$	0.05		3.55	V
	Range		0.03		3.33	v
C <sub>IN2</sub>	LVDS Input Capacitance	IN+ or IN- to V <sub>SS</sub>		3.0		pF
I <sub>IN</sub>	Input Current	$V_{IN} = 3.6V, V_{DD} = 3.6V$	-10		+10	μA
		$V_{IN} = 0V, V_{DD} = 3.6V$	-10		+10	μA

### **Electrical Characteristics** (Continued)

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	Typ (Note 5)	Max	Units
LVDS O	UTPUT DC SPECIFICATIONS	(OUTn±)				
V <sub>OD</sub>	Differential Output Voltage, 0% Pre-emphasis (Note 6)	$R_L = 100\Omega$ external resistor between OUT+ and OUT- Figure 1	250	360	500	mV
$\Delta V_{OD}$	Change in V <sub>OD</sub> between Complementary States		-35		35	mV
V <sub>OS</sub>	Offset Voltage (Note 7)		1.05	1.18	1.475	V
$\Delta V_{OS}$	Change in V <sub>OS</sub> between Complementary States		-35		35	mV
C <sub>OUT</sub>	LVDS Output Capacitance	OUT+ or OUT- to V <sub>SS</sub>		2.5		pF
I <sub>os</sub>	Output Short Circuit Current	OUT+ or OUT- Short to GND		-21	-40	mA
		OUT+ or OUT- Short to VDD		6	40	mA
SUPPLY	CURRENT (Static)			•		
I <sub>cc</sub>	Supply Current	All inputs and outputs enabled and active, terminated with differential load of 100 $\Omega$ between OUT+ and OUT PEM = L		175	215	mA
I <sub>CCZ</sub>	Supply Current - Power Down Mode	PWDN = L, PEM = L		20	200	μA
SWITCH	ING CHARACTERISTICS—L	VDS OUTPUTS				
t <sub>LHT</sub>	Differential Low to High Transition Time (Note 12)	Use an alternating 1 and 0 pattern at 200 Mbps, measure between 20% and 80% of $\rm V_{\rm OD}$ .		170	250	ps
t <sub>HLT</sub>	Differential High to Low Transition Time (Note 12)	Figures 2, 4		170	250	ps
t <sub>PLHD</sub>	Differential Low to High Propagation Delay	Use an alternating 1 and 0 pattern at 200 Mbps, measure at 50% V <sub>OD</sub> between input to output.		1.0	2.0	ns
t <sub>PHLD</sub>	Differential High to Low Propagation Delay	Figures 2, 3		1.0	2.0	ns
t <sub>SKD1</sub>	Pulse Skew (Note 12)	It <sub>PLHD</sub> -t <sub>PHLD</sub> I		10	60	ps
t <sub>SKCC</sub>	Output Channel to Channel Skew (Note 12)	Difference in propagation delay (t <sub>PLHD</sub> or t <sub>PHLD</sub> ) among all output channels.		25	75	ps
t <sub>SKP</sub>	Part to Part Skew (Note 12)	Common edge, parts at same temp and V <sub>CC</sub>			550	ps
t <sub>JIT</sub>	Jitter (0% Pre-emphasis)	RJ - Alternating 1 and 0 at 750 MHz (Note 9)		0.5	1.5	ps
	(Note 8)	DJ - K28.5 Pattern, 1.5 Gbps (Note 10)		14	30	ps
		TJ - PRBS 2 <sup>23</sup> -1 Pattern, 1.5 Gbps (Note 11)		14	31	ps
t <sub>ON</sub>	LVDS Output Enable Time	Time from PWDN to OUT± change from TRI-STATE to active.  Figures 5, 6			20	μs
t <sub>OFF</sub>	LVDS Output Disable Time	Time from PWDN to OUT± change from active to TRI-STATE.  Figures 5, 6			12	ns

- $\textbf{Note 5:} \ \, \textbf{Typical parameters are measured at V}_{DD} = 3.3 \textbf{V}, \, \textbf{T}_{A} = 25 \text{^{\circ}C}. \, \, \textbf{They are for reference purposes, and are not production-tested}.$
- $\textbf{Note 6:} \ \, \text{Differential output voltage V}_{\text{OD}} \text{ is defined as ABS(OUT+-OUT-)}. \ \, \text{Differential input voltage V}_{\text{ID}} \text{ is defined as ABS(IN+-IN-)}.$
- Note 7: Output offset voltage VOS is defined as the average of the LVDS single-ended output voltages at logic high and logic low states.
- Note 8: Jitter is not production tested, but guaranteed through characterization on a sample basis.
- Note 9: Random Jitter, or RJ, is measured RMS with a histogram including 1500 histogram window hits. Stimulus and fixture Jitter has been subtracted. The input voltage =  $V_{ID}$  = 500 mV, input common mode voltage =  $V_{ICM}$  = 1.2V, 50% duty cycle at 750 MHz,  $t_r$  =  $t_f$  = 50 ps (20% to 80%).
- Note 10: Deterministic Jitter, or DJ, is a peak to peak value. Stimulus and fixture jitter has been subtracted. The input voltage =  $V_{ID}$  = 500 mV, input common mode voltage =  $V_{ICM}$  = 1.2V, K28.5 pattern at 1.5 Gbps,  $t_f$  =  $t_f$  = 50 ps (20% to 80%). The K28.5 pattern is repeating bit streams of (0011111010 110000101).
- Note 11: Total Jitter, or TJ, is measured peak to peak with a histogram including 3500 window hits. Stimulus and fixture Jitter has been subtracted. The input voltage =  $V_{ID}$  = 500 mV, input common mode voltage =  $V_{ICM}$  = 1.2V,  $2^{23}$ -1 PRBS pattern at 1.5 Gbps,  $t_r = t_f = 50$  ps (20% to 80%).
- Note 12: Not production tested. Guaranteed by a statistical analysis on a sample basis at the time of characterization.

## **DC Test Circuits**

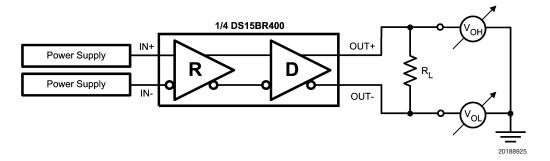


FIGURE 1. Differential Driver DC Test Circuit

## **AC Test Circuits and Timing Diagrams**

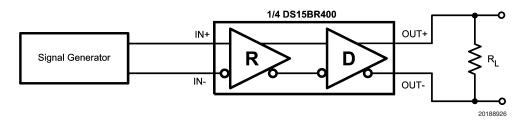


FIGURE 2. Differential Driver AC Test Circuit

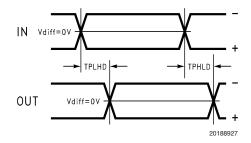


FIGURE 3. Propagation Delay Timing Diagram

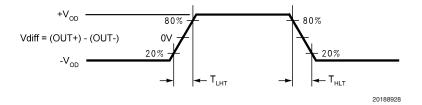


FIGURE 4. LVDS Output Transition Times

## AC Test Circuits and Timing Diagrams (Continued)

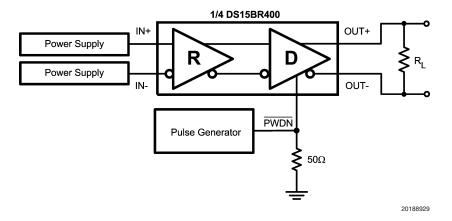


FIGURE 5. Enable/Disable Time Test Circuit

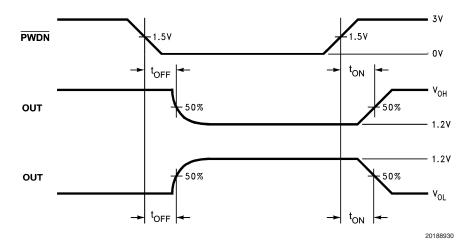


FIGURE 6. Enable/Disable Time Diagram

## **Application Information**

#### **INTERNAL TERMINATIONS**

The DS15BR400 has integrated termination resistors on both the input and outputs. The inputs have a  $100\Omega$  resistor across the differential pair, placing the receiver termination as close as possible to the input stage of the device. The LVDS outputs also contain an integrated  $100\Omega$  ohm termination resistor, this resistor is used to minimize the output return loss and does not take the place of the 100 ohm termination at the inputs to the receiving device. The integrated terminations improve signal integrity and decrease the external component count resulting in space savings. The DS15BR401 has  $100\Omega$  output terminations only.

#### **OUTPUT CHARACTERISTICS**

The output characteristics of the DS15BRB400/DS15BR401 have been optimized for point-to-point backplane and cable applications, and are not intended for multipoint or multidrop signaling.

#### **POWERDOWN MODE**

The PWDN input activates a hardware powerdown mode. When the powerdown mode is active (PWDN=L), all input and output buffers and internal bias circuitry are powered off. When exiting powerdown mode, there is a delay associated with turning on bandgap references and input/output buffer circuits as indicated in the LVDS Output Switching Characteristics

### PRE-EMPHASIS

Pre-emphasis dramatically reduces ISI jitter from long or lossy transmission media. One pin is used to select the pre-emphasis level for all outputs, off or on. The pre-emphasis boost is approximately 6 dB at 750 MHz.

#### **Pre-emphasis Control Selection Table**

PEM	Pre-Emphasis	
0	Off	
1	On	

#### **INPUT FAILSAFE BIASING**

External pull up and pull down resistors may be used to provide enough of an offset to enable an input failsafe under open-circuit conditions. This configuration ties the positive LVDS input pin to  $V_{\rm DD}$  thru a pull up resistor and the negative LVDS input pin is tied to GND by a pull down resistor. The pull up and pull down resistors should be in the  $5k\Omega$  to  $15k\Omega$  range to minimize loading and waveform distortion to the driver. The common-mode bias point ideally should be set to approximately 1.2V. Please refer to application note AN-1194 "Failsafe Biasing of LVDS Interfaces" for more information.

#### **DECOUPLING**

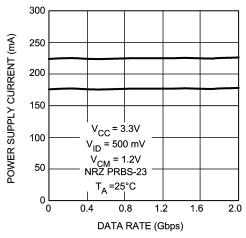
Each power or ground lead of the DS15BR400 should be connected to the PCB through a low inductance path. For best results, one or more vias are used to connect a power or ground pin to the nearby plane. Ideally, via placement is immediately adjacent to the pin to avoid adding trace inductance. Placing power plane closer to the top of the board reduces effective via length and its associated inductance.

Bypass capacitors should be placed close to VDD pins. Small physical size capacitors, such as 0402, X7R, surface mount capacitors should be used to minimize body inductance of capacitors. Each bypass capacitor is connected to the power and ground plane through vias tangent to the pads of the capacitor. An X7R surface mount capacitor of size 0402 has about 0.5 nH of body inductance. At frequencies above 30 MHz or so, X7R capacitors behave as low impedance inductors. To extend the operating frequency range to a few hundred MHz, an array of different capacitor values like 100 pF, 1 nF, 0.03  $\mu$ F, and 0.1  $\mu$ F are commonly used in parallel. The most effective bypass capacitor can be built using sandwiched layers of power and ground at a separation of 2–3 mils. With a 2 mil FR4 dielectric, there is approximately 500 pF per square inch of PCB.

The center dap of the LLP package housing the DS15BR400 should be connected to a ground plane through an array of vias. The via array reduces the effective inductance to ground and enhances the thermal performance of the LLP package.

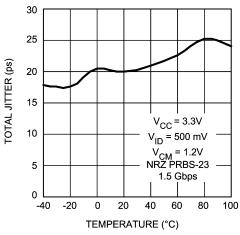
## **Typical Performance Characteristics**

#### Power Supply Current vs. Data Rate



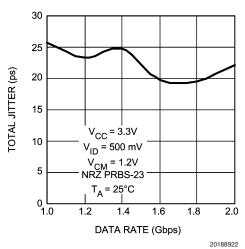
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#### Total Jitter vs. Ambient Temperature

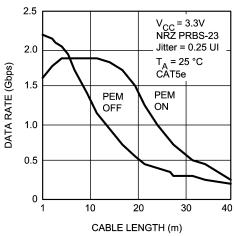


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#### Total Jitter vs. Data Rate



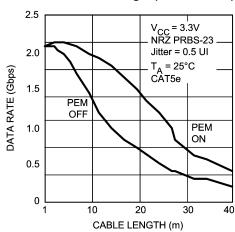
Data Rate vs. Cable Length (0.25 UI Criteria)



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Data presented in this graph was collected using the DS15BR400EVK, a pair of RJ-45 to SMA adapter boards and various length Belden 1700a cables. The maximum data rate was determined based on total jitter (0.25 UI criteria) measured after the cable. The total jitter was a peak to peak value measured with a histogram including 3000 window hits.

#### Data Rate vs. Cable Length (0.5 UI Criteria)



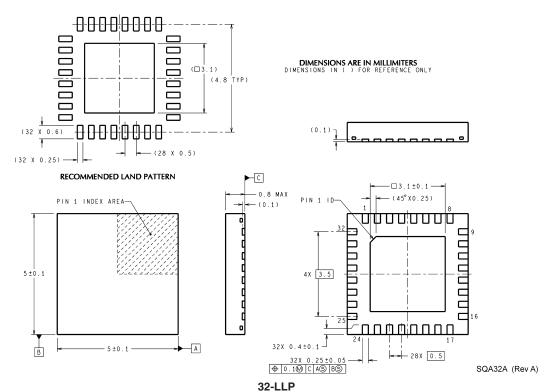
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Data presented in this graph was collected using the DS15BR400EVK, a pair of RJ-45 to SMA adapter boards and various length Belden 1700a cables. The maximum data rate was determined based on total jitter (0.5 Ul criteria) measured after the cable. The total jitter was a peak to peak value measured with a histogram including 3000 window hits.

## Physical Dimensions inches (millimeters) unless otherwise noted A 7 ±0.1 (1.6 TYP) (0.3 TYP) LAND PATTERN RECOMMENDATION PIN #1 IDENT -11°-13° TOP & BOTTOM - 0.5 TYP 0.22±0.05 TYP **♦** 0.08**0** C AS BS R0.08-0.20 GAGE PLANE c L<sub>0.05-0.15</sub> 0.09-0.20 TYP SEATING PLANE -SEE DETAIL A DETAIL A DIMENSIONS ARE IN MILLIMETERS VBC48A (Rev A)

48-TQFP
NS Package Number VBC48a
Order Number DS15BR400TVS, DS15BR401TVS (250 piece Tray)
Order Number DS15BR400TVSX, DS15BR401TVSX (1000 piece Tape and Reel)

### Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



(See AN-1187 for PCB Design and Assembly Recommendations)

NS Package Number SQA32A

Order Number DS15BR400TSQ, DS15BR401TSQ (1000 piece Tape and Reel)

DS15BR400TSQX, DS15BR401TSQX (4500 piece Tape and Reel)

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